

Edward T Yu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

217
papers

9,755
citations

48
h-index

93
g-index

236
ext. papers

10,580
ext. citations

4.9
avg, IF

6.06
L-index

#	Paper	IF	Citations
217	Electronic structure of epitaxially grown and regrown GaN pn junctions characterized by scanning Kelvin probe and capacitance microscopy. <i>Journal of Applied Physics</i> , 2022 , 131, 015704	2.5	1
216	Wafer-Scale Synthesis of WS Films with In Situ Controllable p-Type Doping by Atomic Layer Deposition.. <i>Research</i> , 2021 , 2021, 9862483	7.8	2
215	Electromagnetic Thermal Energy Transfer in Nanoparticle Assemblies Below Diffraction Limit. <i>Journal of Thermal Science and Engineering Applications</i> , 2021 , 13,	1.9	1
214	Cost-effective liquid-junction solar devices with plasma-implanted Ni/TiN/CNF hierarchically structured nanofibers. <i>Journal of Electroanalytical Chemistry</i> , 2021 , 887, 115167	4.1	7
213	Omnidirectional Current Enhancement From Laminated Moth-Eye Textured Polymer Packaging for Large-Area, Flexible III-V Solar Modules. <i>IEEE Journal of Photovoltaics</i> , 2021 , 11, 685-691	3.7	1
212	Scalable, highly stable Si-based metal-insulator-semiconductor photoanodes for water oxidation fabricated using thin-film reactions and electrodeposition. <i>Nature Communications</i> , 2021 , 12, 3982	17.4	3
211	Plasma-implanted Ti-doped hematite photoanodes with enhanced photoelectrochemical water oxidation performance. <i>Journal of Alloys and Compounds</i> , 2021 , 870, 159376	5.7	6
210	Growth Mechanisms and Morphology Engineering of Atomic Layer-Deposited WS. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 43115-43122	9.5	2
209	Zeta Potential Dependent Self-Assembly for Very Large Area Nanosphere Lithography. <i>Nano Letters</i> , 2020 , 20, 5090-5096	11.5	14
208	Out-of-plane electromechanical coupling in transition metal dichalcogenides. <i>Applied Physics Letters</i> , 2020 , 116, 053101	3.4	11
207	Hyperspectral imaging for high-throughput, spatially resolved spectroscopic scatterometry of silicon nanopillar arrays. <i>Optics Express</i> , 2020 , 28, 14209-14221	3.3	6
206	Strain-dependent luminescence and piezoelectricity in monolayer transition metal dichalcogenides. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 042205	1.3	3
205	Composition-dependent structural transition in epitaxial Bi _{1-x} Sb _x thin films on Si(111). <i>Physical Review Materials</i> , 2019 , 3,	3.2	3
204	Effect of particle size distribution on near-field thermal energy transfer within the nanoparticle packings. <i>Journal of Photonics for Energy</i> , 2019 , 9, 1	1.2	8
203	Electrodeposition of crystalline silicon films from silicon dioxide for low-cost photovoltaic applications. <i>Nature Communications</i> , 2019 , 10, 5772	17.4	32
202	Highly improved passivation of c-Si surfaces using a gradient i a-Si:H layer. <i>Journal of Applied Physics</i> , 2018 , 123, 163101	2.5	4
201	Probing nanoscale variations in strain and band structure of MoS ₂ on Au nanopyramids using tip-enhanced Raman spectroscopy. <i>Physical Review B</i> , 2018 , 97,	3.3	4

200	Improved Performance of Zinc Oxide Thin Film Transistor Pressure Sensors and a Demonstration of a Commercial Chip Compatibility with the New Force Sensing Technology. <i>Advanced Materials Technologies</i> , 2018 , 3, 1700279	6.8	33
199	Crystalline SrZrO ₃ deposition on Ge (001) by atomic layer deposition for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2018 , 124, 044102	2.5	9
198	Uncertainty Analysis of Near-Field Thermal Energy Transfer within Nanoparticle Packing 2018 ,		1
197	Structural coloration with hourglass-shaped vertical silicon nanopillar arrays. <i>Optics Express</i> , 2018 , 26, 30952-30968	3.3	12
196	Influence of the Substrate to the LSP Coupling Wavelength and Strength. <i>Nanoscale Research Letters</i> , 2018 , 13, 280	5	4
195	Ultra-stable 2D layered methylammonium cadmium trihalide perovskite photoelectrodes. <i>Journal of Materials Chemistry C</i> , 2018 , 6, 11552-11560	7.1	13
194	Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl ₂ -based Molten Salt. <i>Angewandte Chemie</i> , 2017 , 129, 15274-15278	3.6	7
193	Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl ₂ -based Molten Salt. <i>Angewandte Chemie - International Edition</i> , 2017 , 56, 15078-15082	16.4	39
192	Out-of-Plane Electromechanical Response of Monolayer Molybdenum Disulfide Measured by Piezoresponse Force Microscopy. <i>Nano Letters</i> , 2017 , 17, 5464-5471	11.5	71
191	Electrochemical Formation of a p-n Junction on Thin Film Silicon Deposited in Molten Salt. <i>Journal of the American Chemical Society</i> , 2017 , 139, 16060-16063	16.4	39
190	Localized dielectric breakdown and antireflection coating in metal-oxide-semiconductor photoelectrodes. <i>Nature Materials</i> , 2017 , 16, 127-131	27	50
189	Optimization of Lead-free Organic-Inorganic Tin(II) Halide Perovskite Semiconductors by Scanning Electrochemical Microscopy. <i>Electrochimica Acta</i> , 2016 , 220, 205-210	6.7	34
188	A Low-Leakage Epitaxial High- κ Gate Oxide for Germanium Metal-Oxide-Semiconductor Devices. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 5416-23	9.5	7
187	Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with SrHf _x Ti _{1-x} O ₃ . <i>MRS Communications</i> , 2016 , 6, 125-132	2.7	13
186	Optimization of PbI ₂ /MAPbI ₃ Perovskite Composites by Scanning Electrochemical Microscopy. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 19890-19895	3.8	42
185	A Liquid Junction Photoelectrochemical Solar Cell Based on p-Type MeNH ₃ PbI ₃ Perovskite with 1.05 V Open-Circuit Photovoltage. <i>Journal of the American Chemical Society</i> , 2015 , 137, 14758-64	16.4	41
184	Cross-sectional scanning thermal microscopy of ErAs/GaAs superlattices grown by molecular beam epitaxy. <i>Nanotechnology</i> , 2015 , 26, 265701	3.4	9
183	A silicon-based photocathode for water reduction with an epitaxial SrTiO ₃ protection layer and a nanostructured catalyst. <i>Nature Nanotechnology</i> , 2015 , 10, 84-90	28.7	292

182	Asymmetric light reflectance from metal nanoparticle arrays on dielectric surfaces. <i>Scientific Reports</i> , 2015 , 5, 18331	4.9	21
181	Interface Adhesion between 2D Materials and Elastomers Measured by Buckle Delaminations. <i>Advanced Materials Interfaces</i> , 2015 , 2, 1500176	4.6	66
180	Subwavelength nanostructures integrated with polymer-packaged iii-v solar cells for omnidirectional, broad-spectrum improvement of photovoltaic performance. <i>Progress in Photovoltaics: Research and Applications</i> , 2015 , 23, 1398-1405	6.8	12
179	Strain and Hole Gas Induced Raman Shifts in Ge-Si(x)Ge(1-x) Core-Shell Nanowires Using Tip-Enhanced Raman Spectroscopy. <i>Nano Letters</i> , 2015 , 15, 4303-10	11.5	5
178	Integration of subwavelength optical nanostructures for improved antireflection performance of mechanically flexible GaAs solar cells fabricated by epitaxial lift-off. <i>Solar Energy Materials and Solar Cells</i> , 2015 , 143, 567-572	6.4	5
177	Atomic layer deposition of crystalline SrHfO ₃ directly on Ge (001) for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2015 , 117, 054101	2.5	39
176	Angular dependence of light trapping in In _{0.3} Ga _{0.7} As/GaAs quantum-well solar cells. <i>Journal of Applied Physics</i> , 2014 , 115, 044303	2.5	6
175	Resistive switching of SiO _x with one diode-one resistor nanopillar architecture fabricated via nanosphere lithography 2014 ,		2
174	Highly controllable and stable quantized conductance and resistive switching mechanism in single-crystal TiO ₂ resistive memory on silicon. <i>Nano Letters</i> , 2014 , 14, 4360-7	11.5	101
173	Integrated one diode-one resistor architecture in nanopillar SiO _x resistive switching memory by nanosphere lithography. <i>Nano Letters</i> , 2014 , 14, 813-8	11.5	85
172	Epitaxy: A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors (Adv. Mater. Interfaces 8/2014). <i>Advanced Materials Interfaces</i> , 2014 , 1, n/a-n/a	4.6	1
171	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. <i>Advanced Materials Interfaces</i> , 2014 , 1, 1400081	4.6	38
170	Increased InAs quantum dot size and density using bismuth as a surfactant. <i>Applied Physics Letters</i> , 2014 , 105, 253104	3.4	12
169	Epitaxial c-axis oriented BaTiO ₃ thin films on SrTiO ₃ -buffered Si(001) by atomic layer deposition. <i>Applied Physics Letters</i> , 2014 , 104, 082910	3.4	51
168	Minimized open-circuit voltage reduction in GaAs/InGaAs quantum well solar cells with bandgap-engineered graded quantum well depths. <i>Applied Physics Letters</i> , 2014 , 105, 123906	3.4	2
167	Quantum state engineering with ultra-short-period (AlN) _m /(GaN) _n superlattices for narrowband deep-ultraviolet detection. <i>Nanoscale</i> , 2014 , 6, 14733-9	7.7	13
166	Fabrication of birefringent nanocylinders for single-molecule force and torque measurement. <i>Nanotechnology</i> , 2014 , 25, 235304	3.4	7
165	Oxygen-induced bi-modal failure phenomenon in SiO _x -based resistive switching memory. <i>Applied Physics Letters</i> , 2013 , 103, 033521	3.4	28

164	High ON/OFF Ratio and Quantized Conductance in Resistive Switching of TiO_2 on Silicon. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1385-1387	4.4	29
163	Flexible, low-loss, large-area, wide-angle, wavelength-selective plasmonic multilayer metasurface. <i>Journal of Applied Physics</i> , 2013 , 114, 133104	2.5	20
162	Voltage-controlled ferromagnetism and magnetoresistance in $\text{LaCoO}_3/\text{SrTiO}_3$ heterostructures. <i>Journal of Applied Physics</i> , 2013 , 114, 183909	2.5	12
161	Electrochemical Monitoring of TiO_2 Atomic Layer Deposition by Chronoamperometry and Scanning Electrochemical Microscopy. <i>Chemistry of Materials</i> , 2013 , 25, 4165-4172	9.6	20
160	Large-area omnidirectional antireflection coating on low-index materials. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 2584	1.7	12
159	Wide-angle wavelength-selective multilayer optical metasurfaces robust to interlayer misalignment. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 27	1.7	11
158	Light trapping in thin-film solar cells via scattering by nanostructured antireflection coatings. <i>Journal of Applied Physics</i> , 2013 , 114, 044310	2.5	33
157	Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO_x -based resistive switching memory. <i>Applied Physics Letters</i> , 2013 , 103, 193508	3.4	25
156	Quantitative scanning thermal microscopy of ErAs/GaAs superlattice structures grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 061912	3.4	7
155	Computational analysis of thin film InGaAs/GaAs quantum well solar cells with back side light trapping structures. <i>Optics Express</i> , 2012 , 20 Suppl 6, A864-78	3.3	9
154	Semiconductor heterostructures and optimization of light-trapping structures for efficient thin-film solar cells. <i>Journal of Optics (United Kingdom)</i> , 2012 , 14, 024007	1.7	9
153	Conductivity and structure of ErAs nanoparticles embedded in GaAs pn junctions analyzed via conductive atomic force microscopy. <i>Applied Physics Letters</i> , 2012 , 100, 233117	3.4	4
152	Experimental realization and modeling of a subwavelength frequency-selective plasmonic metasurface. <i>Applied Physics Letters</i> , 2011 , 99, 221106	3.4	37
151	Photon management for photovoltaics. <i>MRS Bulletin</i> , 2011 , 36, 424-428	3.2	61
150	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 4384-4392	2.9	22
149	Improvement of performance of InAs quantum dot solar cell by inserting thin AlAs layers. <i>Nanoscale Research Letters</i> , 2011 , 6, 83	5	9
148	Scanning capacitance microscopy of ErAs nanoparticles embedded in GaAs pn junctions. <i>Applied Physics Letters</i> , 2011 , 99, 133114	3.4	5
147	Ballistic transport and electrical spin signal enhancement in a nanoscale three-terminal spintronic device. <i>Applied Physics Letters</i> , 2011 , 98, 142115	3.4	3

146	Tunneling MOSFETs Based on III-V Staggered Heterojunctions. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1252, 4		
145	Low defect-mediated reverse-bias leakage in (0001) GaN via high-temperature molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010 , 96, 102111	3-4	34
144	Engineering of plasmonic effects in photodetectors and high-efficiency photovoltaics 2010 ,		1
143	Influence of surface treatment and interface layers on electrical spin injection efficiency and transport in InAs. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 1164-1168	1-3	2
142	Toward high-efficiency quantum dot solar cells: optimized gratings for ultrathin waveguide devices 2010 ,		1
141	Design of Tunneling Field-Effect Transistors Based on Staggered Heterojunctions for Ultralow-Power Applications. <i>IEEE Electron Device Letters</i> , 2010 , 31, 431-433	4-4	94
140	Scanning tunneling spectroscopy and Kelvin probe force microscopy investigation of Fermi energy level pinning mechanism on InAs and InGaAs clean surfaces. <i>Journal of Applied Physics</i> , 2010 , 108, 023711	2-5	60
139	Ultraviolet and solar-blind spectral imaging with subwavelength transmission gratings. <i>Applied Physics Letters</i> , 2009 , 95, 161107	3-4	6
138	Scanning capacitance characterization of potential screening in InAs nanowire devices. <i>Journal of Applied Physics</i> , 2009 , 105, 014306	2-5	3
137	Determination of Thermal Parameters of Nanostructures Exhibiting One-Dimensional Heat Flow Through a Thermal Transient Method. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1172, 54		
136	Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. <i>Advanced Functional Materials</i> , 2009 , 19, 2102-2108	15-6	82
135	Determination of thermal parameters of one-dimensional nanostructures through a thermal transient method. <i>Journal of Thermal Analysis and Calorimetry</i> , 2009 , 97, 1023-1026	4-1	4
134	Transport coefficients of InAs nanowires as a function of diameter. <i>Small</i> , 2009 , 5, 77-81	11	60
133	Precise semiconductor nanowire placement through dielectrophoresis. <i>Nano Letters</i> , 2009 , 9, 2260-6	11-5	154
132	Surface diffusion and substrate-nanowire adatom exchange in InAs nanowire growth. <i>Nano Letters</i> , 2009 , 9, 1967-72	11-5	70
131	Light scattering into silicon-on-insulator waveguide modes by random and periodic gold nanodot arrays. <i>Journal of Applied Physics</i> , 2009 , 105, 073101	2-5	21
130	Field dependent transport properties in InAs nanowire field effect transistors. <i>Nano Letters</i> , 2008 , 8, 3114-9	11-5	30
129	Integration of vertical InAs nanowire arrays on insulator-on-silicon for electrical isolation. <i>Applied Physics Letters</i> , 2008 , 93, 203109	3-4	15

128	InP nanowire/polymer hybrid photodiode. <i>Nano Letters</i> , 2008 , 8, 775-9	11.5	157
127	Nanoparticle-induced light scattering for improved performance of quantum-well solar cells. <i>Applied Physics Letters</i> , 2008 , 93, 091107	3.4	116
126	Plasmonic nanoparticle scattering for enhanced performance of photovoltaic and photodetector devices 2008 ,		28
125	Metal and dielectric nanoparticle scattering for improved optical absorption in photovoltaic devices. <i>Applied Physics Letters</i> , 2008 , 93, 113108	3.4	199
124	Characterization of nanoscale electronic structure in nonpolar GaN using scanning capacitance microscopy. <i>Journal of Applied Physics</i> , 2008 , 103, 014305	2.5	6
123	Growth of InAs Nanowires on SiO ₂ Substrates: Nucleation, Evolution, and the Role of Au Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2007 , 111, 13331-13336	3.8	35
122	III-V nanowire growth mechanism: V/III ratio and temperature effects. <i>Nano Letters</i> , 2007 , 7, 2486-90	11.5	156
121	High electron mobility InAs nanowire field-effect transistors. <i>Small</i> , 2007 , 3, 326-32	11	268
120	Excess indium and substrate effects on the growth of InAs nanowires. <i>Small</i> , 2007 , 3, 1683-7	11	30
119	Transport properties of InAs nanowire field effect transistors: The effects of surface states. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 1432		67
118	Photocurrent spectroscopy of optical absorption enhancement in silicon photodiodes via scattering from surface plasmon polaritons in gold nanoparticles. <i>Journal of Applied Physics</i> , 2007 , 101, 104309	2.5	291
117	Analysis of local carrier modulation in InAs semiconductor nanowire transistors. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 1427		5
116	Scanning gate microscopy of InAs nanowires. <i>Applied Physics Letters</i> , 2007 , 90, 233118	3.4	15
115	Influence of surface states on the extraction of transport parameters from InAs nanowire field effect transistors. <i>Applied Physics Letters</i> , 2007 , 90, 162112	3.4	101
114	Dependence of local electronic structure in p-type GaN on crystal polarity and presence of inversion domain boundaries. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 245		1
113	Scanned electrical probe characterization of carrier transport behavior in InAs nanowires. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2036		16
112	Critical dimensions in coherently strained coaxial nanowire heterostructures. <i>Journal of Applied Physics</i> , 2006 , 99, 114308	2.5	111
111	Demonstration and analysis of reduced reverse-bias leakage current via design of nitride semiconductor heterostructures grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 99, 014501	2.5	9

110	Calculation of critical dimensions for wurtzite and cubic zinc blende coaxial nanowire heterostructures. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2053		42
109	Analysis of leakage current mechanisms in Schottky contacts to GaN and Al _{0.25} Ga _{0.75} N/GaN grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 99, 023703	2.5	227
108	Direct observation of ballistic and drift carrier transport regimes in InAs nanowires. <i>Applied Physics Letters</i> , 2006 , 89, 053113	3.4	77
107	Defects in nitride semiconductors: From nanoscale imaging to macroscopic device behavior. <i>Materials Science in Semiconductor Processing</i> , 2006 , 9, 308-314	4.3	6
106	Improved performance of amorphous silicon solar cells via scattering from surface plasmon polaritons in nearby metallic nanoparticles. <i>Applied Physics Letters</i> , 2006 , 89, 093103	3.4	603
105	Enhanced semiconductor optical absorption via surface plasmon excitation in metal nanoparticles. <i>Applied Physics Letters</i> , 2005 , 86, 063106	3.4	910
104	Imaging of thickness and compositional fluctuations in InGa _{0.5} N/GaN quantum wells by scanning capacitance microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1808		
103	Observation of In concentration variations in InGa _{0.5} N/GaN quantum-well heterostructures by scanning capacitance microscopy. <i>Applied Physics Letters</i> , 2005 , 86, 202113	3.4	7
102	Analysis of interface electronic structure in In _x Ga _{1-x} N/GaN heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 2169		7
101	Local conductivity and surface photovoltage variations due to magnesium segregation in p-type GaN. <i>Journal of Applied Physics</i> , 2004 , 95, 6225-6231	2.5	19
100	Observation of subsurface monolayer thickness fluctuations in InGa _{0.5} N/GaN quantum wells by scanning capacitance microscopy and spectroscopy. <i>Applied Physics Letters</i> , 2004 , 85, 407-409	3.4	20
99	Analysis of reverse-bias leakage current mechanisms in GaN grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004 , 84, 535-537	3.4	225
98	Measurement of polarization charge and conduction-band offset at In _x Ga _{1-x} N/GaN heterojunction interfaces. <i>Applied Physics Letters</i> , 2004 , 84, 4644-4646	3.4	116
97	Nanoscale current transport in epitaxial SrTiO ₃ on n ⁺ -Si investigated with conductive atomic force microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 2030		20
96	Influence of AlN buffer on electronic properties and dislocation microstructure of AlGa _{0.5} N/GaN grown by molecular beam epitaxy on SiC. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003 , 21, 1818		6
95	Correlated scanning Kelvin probe and conductive atomic force microscopy studies of dislocations in gallium nitride. <i>Journal of Applied Physics</i> , 2003 , 94, 1448-1453	2.5	170
94	Origin and microscopic mechanism for suppression of leakage currents in Schottky contacts to GaN grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2003 , 94, 7611	2.5	36
93	Reverse-bias leakage current reduction in GaN Schottky diodes by electrochemical surface treatment. <i>Applied Physics Letters</i> , 2003 , 82, 1293-1295	3.4	46

92	Scanning Kelvin probe microscopy of surface electronic structure in GaN grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2002 , 91, 9924	2.5	38
91	Cross-sectional scanning tunneling microscopy of GaAsSb/GaAs quantum well structures. <i>Journal of Applied Physics</i> , 2002 , 92, 3761-3770	2.5	13
90	Direct measurement of the polarization charge in AlGaIn/GaN heterostructures using capacitance-voltage carrier profiling. <i>Applied Physics Letters</i> , 2002 , 80, 3551-3553	3.4	38
89	Reduction of reverse-bias leakage current in Schottky diodes on GaN grown by molecular-beam epitaxy using surface modification with an atomic force microscope. <i>Journal of Applied Physics</i> , 2002 , 91, 9821	2.5	85
88	Direct measurement and characterization of n+ superhalo implants in a 120 nm gate-length Si metal-oxide-semiconductor field-effect transistor using cross-sectional scanning capacitance microscopy. <i>Applied Physics Letters</i> , 2002 , 81, 3993-3995	3.4	18
87	Scanning capacitance spectroscopy of an Al _x Ga _{1-x} N/GaN heterostructure field-effect transistor structure: Analysis of probe tip effects. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 1671		12
86	Distinguishing negatively-charged and highly conductive dislocations in gallium nitride using scanning Kelvin probe and conductive atomic force microscopy. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 743, L2.4.1		0
85	Miscut-angle dependence of perpendicular magnetic anisotropy in thin epitaxial CoPt ₃ films grown on vicinal MgO. <i>Applied Physics Letters</i> , 2002 , 81, 517-519	3.4	16
84	Quantitative analysis of nanoscale electronic properties in an Al _x Ga _{1-x} N/GaN heterostructure field-effect transistor structure. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 1671		6
83	Localized variations in electronic structure of AlGaIn/GaN heterostructures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001 , 79, 2749-2751	3.4	8
82	Influence of surface processing and passivation on carrier concentrations and transport properties in AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2001 , 90, 1357-1361	2.5	47
81	Influence of the dipole interaction energy on clustering in In _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 2001 , 78, 2303-2305	3.4	6
80	Lateral variations in threshold voltage of an Al _x Ga _{1-x} N/GaN heterostructure field-effect transistor measured by scanning capacitance spectroscopy. <i>Applied Physics Letters</i> , 2001 , 78, 88-90	3.4	57
79	Polarization charges and polarization-induced barriers in Al _x Ga _{1-x} N/GaN and In _y Ga _{1-y} N/GaN heterostructures. <i>Applied Physics Letters</i> , 2001 , 79, 2916-2918	3.4	8
78	Frequency Response of Trap States in an Al _x Ga _{1-x} N/GaN Heterostructure Field-Effect Transistor Measured at the Nanoscale by dC/dV Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 680, 1		1
77	Long Time-Constant Trap Effects in Nitride Heterostructure Field Effect Transistors. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 622, 6281		7
76	Enhancement of base conductivity via the piezoelectric effect in AlGaIn/GaN HBTs. <i>Solid-State Electronics</i> , 2000 , 44, 211-219	1.7	32
75	Local electronic properties of AlGaIn/GaN heterostructures probed by scanning capacitance microscopy. <i>Journal of Electronic Materials</i> , 2000 , 29, 274-280	1.9	11

74	Proximal probe characterization of nanoscale charge transport properties in Co/SiO ₂ multilayer structures. <i>Journal of Electronic Materials</i> , 2000 , 29, 1299-1303	1.9	3
73	Charging effects in AlGa _N /Ga _N heterostructures probed using scanning capacitance microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 2304		13
72	Characterization of Al _x Ga _{1-x} As/GaAs heterojunction bipolar transistor structures using cross-sectional scanning force microscopy. <i>Journal of Applied Physics</i> , 2000 , 87, 1937-1942	2.5	24
71	Characterization and analysis of a novel hybrid magnetoelectronic device for magnetic field sensing. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000 , 18, 1834-1837	2.9	4
70	Trap characterization by gate-drain conductance and capacitance dispersion studies of an AlGa _N /Ga _N heterostructure field-effect transistor. <i>Journal of Applied Physics</i> , 2000 , 87, 8070-8073	2.5	99
69	Gate leakage current mechanisms in AlGa _N /Ga _N heterostructure field-effect transistors. <i>Journal of Applied Physics</i> , 2000 , 88, 5951-5958	2.5	158
68	Cross-sectional scanning tunneling microscopy of InAsSb/InAsP superlattices. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1781		7
67	Scanning capacitance microscopy of AlGa _N /Ga _N heterostructure field-effect transistor epitaxial layer structures. <i>Applied Physics Letters</i> , 1999 , 75, 2250-2252	3.4	21
66	Charge storage in Co nanoclusters embedded in SiO ₂ by scanning force microscopy. <i>Applied Physics Letters</i> , 1999 , 74, 472-474	3.4	102
65	A monolithic field-effect-transistor-amplified magnetic field sensor. <i>Applied Physics Letters</i> , 1999 , 75, 731-733	3.4	3
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